

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	6	"6,014,030"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 10:25
S2	929	324/713	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 10:32
S3	757	361/93.1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 09:30
S4	4442	current adj (sense sensing) adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 09:21
S5	178	current adj (sense sensing) near (MOS MOSFET FET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 09:22
S6	0	current adj (sense sensing) near (MOS MOSFET FET field adj effect) near switch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 09:23
S7	36	current adj (sense sensing) near (MOS MOSFET FET field adj effect) same switch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:29
S8	4	"5,986,441"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:24
S9	5	("4914542" "5004970" "5008586" "5164659" "5220207").PN.	USPAT	OR	ON	2004/08/31 11:15
S10	10	"5,805,434"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:26

S11	3	"6,282,107"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:28
S12	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT	OR	ON	2004/08/31 11:26
S13	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT	OR	ON	2004/08/31 11:27
S14	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT	OR	ON	2004/08/31 11:27
S15	2179645	current adj (sense sensing) near across (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:30
S16	3	current adj (sense sensing) near across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:42
S17	14	over adj current same voltage adj across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:07
S18	14	over adj current same voltage near across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:11
S19	5	("4479083" "4502000" "4502001" "4949028" "4967136").PN.	USPAT	OR	ON	2004/08/31 12:09
S20	22	"5528122".URPN.	USPAT	OR	ON	2004/08/31 12:10
S21	22	"5528122".URPN.	USPAT	OR	ON	2004/08/31 12:10

S22	130	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:11
S23	92	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) and temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:12
S24	11	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) same temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:27
S25	5	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) and temperature adj (sense sensing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:35
S26	1	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:15
S27	4	("5530335" "5554919" "5721480" "5736832").PN.	USPAT	OR	ON	2004/08/31 12:54
S28	3	"6014030".URPN.	USPAT	OR	ON	2004/08/31 12:56
S29	3	"6014030".URPN.	USPAT	OR	ON	2004/08/31 12:56
S30	5	over adj current and voltage near (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:34
S31	106644	voltage adj across (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:34
S32	14	voltage adj across adj (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:37
S33	0	voltage adj across adj (MOS MOSFET FET field adj effect switch) same temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:38

S34	502	temperature adj (compensate compensating) adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:39
S35	0	temperature adj (compensate compensating) adj resistor same operational adj amplifier same voltage adj drop near (MOS FET MOSFET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:40
S36	0	temperature adj (compensate compensating) adj resistor same voltage adj drop near (MOS FET MOSFET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:40
S37	0	temperature adj (compensate compensating) adj resistor and voltage adj drop near (MOS FET MOSFET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:41
S38	40	temperature adj (compensate compensating) adj resistor same operational adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 15:57
S39	17	temperature adj (compensate compensating) adj resistor same current adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 16:03
S40	20	temperature adj (compensate compensating) near resistor same current adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 16:25
S41	354	324/705	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 16:25
S42	187	current adj (limit limiting) and switch near across near voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:48
S43	95	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:48

S44	28	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj divider	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:49
S45	28	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:54
S46	0	current adj (limit limiting) near transistor and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:55
S47	0	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:56
S48	8	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:57
S49	53	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:58
S50	1	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 16:02
S51	3	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near (MOS MOSFET field adj effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 16:04
S52	900	361/93.1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/23 13:01

S53	196	361/93.7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/23 16:31
S54	429	324/705	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/26 10:19
S55	1024	324/713	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/26 10:52